

IN THE CLAIMS

Cancel claims 10 and 19 without prejudice.

Please use the following claims to replace those of the same number and add any claims that have new numbers:

Sub C1
A1
1. (Amended) A semiconductor device, comprising:

- a substrate having circuitry formed therein;
- a passivation layer formed overlying at least a portion of the substrate;
- a fuse, which may be selectively open-circuited, formed overlying the passivation layer;
- and
- a packaging material formed on the fuse.

Sub C2
A2
11. A semiconductor device, comprising:

- a substrate having a first circuit formed therein and a second circuit formed therein, wherein the first circuit has a first contact area and the second circuit has a second contact area;
- a passivation layer formed overlying at least a portion of the substrate;
- a fuse, which may be selectively open-circuited, formed overlying the passivation layer, the fuse having a third contact area which is electrically coupled to the first contact area of the first circuit, and the fuse having a fourth contact area which is electrically coupled to the second contact area of the second circuit, wherein the first contact area of the first circuit and the second contact area of the second circuit are no longer electrically connected if the fuse is open-circuited; and
- a packaging material formed on the fuse.

Sub C3
A3
18. A method for forming a semiconductor device having a fuse, comprising:

- providing a substrate;
- forming a passivation layer overlying at least a portion of the substrate;
- forming the fuse overlying the passivation layer; and
- forming a packaging material on the fuse.